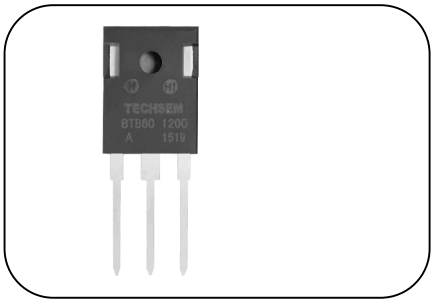


Features：

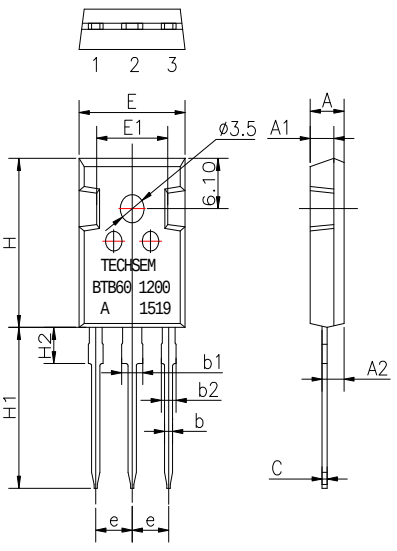
- **n** Two anti-paralled thyristors on one Si-wafer
- **n** Hermetic metal cases with ceramic

Typical Applications

- **n** High power industrical and power transmissior
- **n** DC and AC motor control
- **n** AC controllers

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(RMS)}$	RMS current	full sine wave Single side cooled, T_C=75°C	125			60	A
V_{DRM} V_{RRM}	Repetitive peak reverse voltage	V_{DRM} tp=10ms V_{DSM} = V_{DRM} +100V	125	800		1800	V
I_{DRM} I_{RRM}	Repetitive peak current	V_{DM}= V_{DRM}	125			0.8	mA
I_{TSM}	Surge on-state current	10ms half sine wave V_R=0.6V_{RRM}	125			600	A
I^2t	I^2T for fusing coordination					1800	A^2s
V_{TM}	Peak on-state voltage	I_{TM}=90A, tp=10ms	25			1.65	V
dv/dt	Critical rate of rise of off-state voltage	V_{DM}=0.67V_{DRM} gate open	125	1000			V/μs
di/dt	Critical rate of rise of on-state current		125	20			A/μs
I_{GT}	Gate trigger current	V_D=12V_{DC}, R_L=33Ω Ⅰ - Ⅱ -Ⅲ	25			50	mA
V_{GT}	Gate trigger voltage					1.3	V
I_H	Holding current	V_D=12V_{DC}, R_L=33Ω				60	mA
I_{GM}	Peak gate current	tp=20μs	125			8	A
P_{GM}	Peak gate power	tp=20μs	125			10	w
$P_{G(AV)}$	Average gate power dissipation		125			2	w
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled				0.45	°C /W
$R_{th(j-a)}$	Thermal resistance Junction to ambient					40	
Tj	Operating Junction temperature			-40		125	
T_{stg}	Stored temperature	单位 mm		-40		150	°C
Outline	TO-247AA						

Outline:



	单位 mm		
	MIN	NOM	MAX
A	4.8	5	5.2
A1	3.3	3.5	3.7
A2	2.1	2.3	2.5
b	1	1.2	1.4
b1	2.9	3.1	3.3
b2	1.9	2.1	2.3
c	0.4	0.6	0.8
e	5.25	5.45	5.65
E	15.6	15.8	16
E1	10.6	10.8	11
H	20.8	21	21.2
H1	19.4	19.9	20.4
H2	3.9	4.1	4.3
G	5.9	6.1	6.3
?P	3.3	3.5	3.7